

BCM120S20D2

Silicon Carbide Schottky Diode

1200 V, 20 A

Description

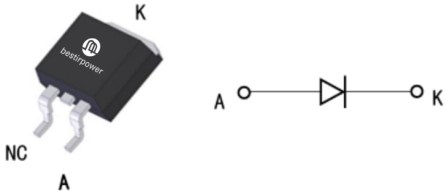
BCM120S20D2 utilizes bestirpower's advanced silicon carbide diode technology. This technology combines the benefits of excellent low forward voltage and robustness. Consequently, the family is suitable for application requiring high power efficiency

Applications

- Solar inverter, UPS
- EV charging station
- Power Factor Correction
- No reverse recovery current
- Low forward voltage
- 175°C Max junction temperature
- High surge current capability
- Switching behavior independent of temperature
- Halogen Free and RoHS compliant

Features

V_{RRM}	I_F	T_C	Q_C
1200 V	20 A	150 °C	121 nC



Absolute Maximum Ratings ($T_C = 25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter		Value	Unit
V_{RRM}	Repetitive Peak Reverse Voltage		1200	V
I_F	Forward Current	$T_C = 25^{\circ}\text{C}$	58	A
		$T_C = 135^{\circ}\text{C}$	25	A
		$T_C = 150^{\circ}\text{C}$	20	A
$I_{F,SM}$	Non-Repetitive Forward Surge Current	$T_C = 25^{\circ}\text{C}, t_p = 10\text{ ms}$	135	A
		$T_C = 110^{\circ}\text{C}, t_p = 10\text{ ms}$	115	A
$I_{F,Max}$	Non-Repetitive Peak Forward Current	$T_C = 25^{\circ}\text{C}, t_p = 10\text{ }\mu\text{s}$	1180	A
		$T_C = 150^{\circ}\text{C}, t_p = 10\text{ }\mu\text{s}$	980	A
I^2dt value	$\int I^2 dt$	$T_C = 25^{\circ}\text{C}, t_p = 10\text{ ms}$	91	A^2s
		$T_C = 150^{\circ}\text{C}, t_p = 10\text{ ms}$	66	A^2s
P_{tot}	Power Dissipation	$T_C = 25^{\circ}\text{C}$	273	W
T_J, T_{STG}	Operating Junction and Storage Temperature		-55 to +175	$^{\circ}\text{C}$

Thermal Characteristics

Symbol	Parameter	Value	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	0.55	$^{\circ}\text{C/W}$

Electrical Characteristics (T_J = 25°C unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
V _F	Forward Voltage	I _F = 20 A, T _J = 25°C	-	1.39	1.70	V
		I _F = 20 A, T _J = 175°C	-	1.8	-	
I _R	Reverse Current	V _R = 1200 V, T _J = 25°C	-	10	100	µA
		V _R = 1200 V, T _J = 175°C	-	-	300	
Q _C	Total Capacitive Charge	V _R = 800 V, T _J = 25°C	-	121	-	nC
C	Total Capacitance	V _R = 1 V, f = 100 kHz	-	1357	-	pF
		V _R = 800 V, f = 100 kHz	-	85	-	
E _C	Capacitance Stored Energy	V _R = 800 V, T _c = 25°C	-	34	-	µJ

Typical Performance Characteristics

Figure 1. Power Derating

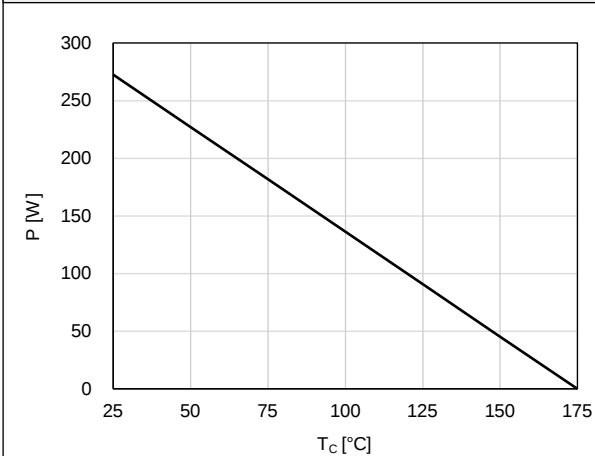


Figure 2. Current Derating

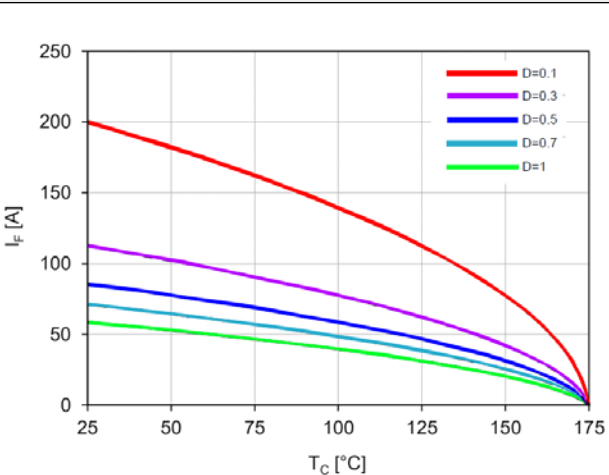


Figure 3. Forward Characteristics

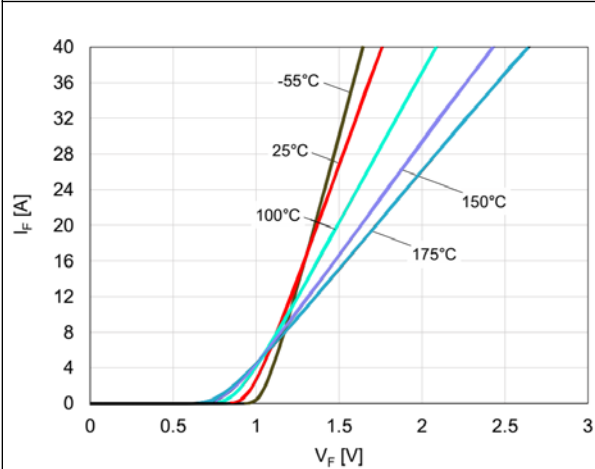


Figure 4. Reverse Characteristics

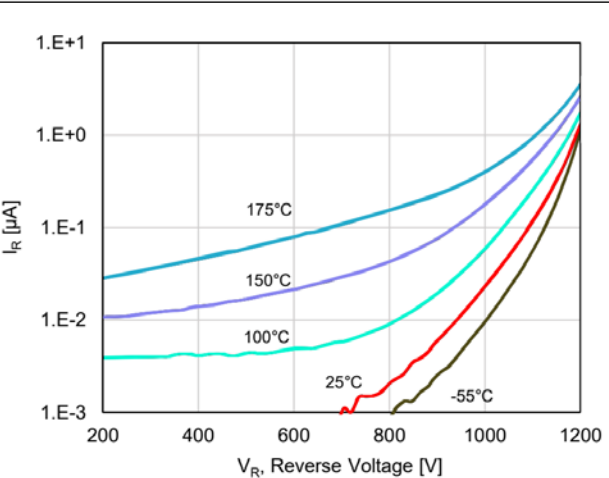


Figure 5. Capacitive Charge Characteristics

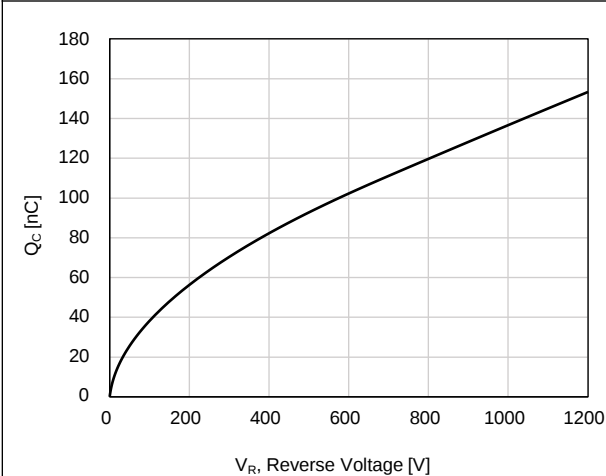
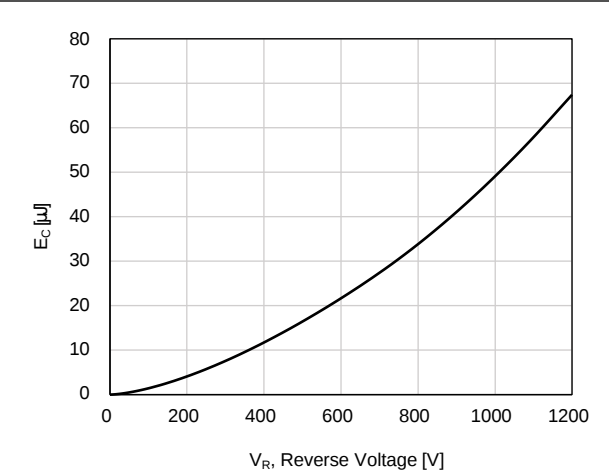


Figure 6. Capacitance Stored Energy



Typical Performance Characteristics

Figure 7. Capacitance Characteristics

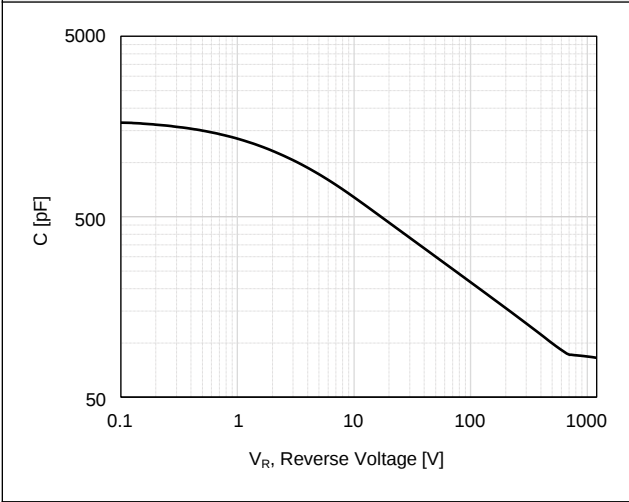
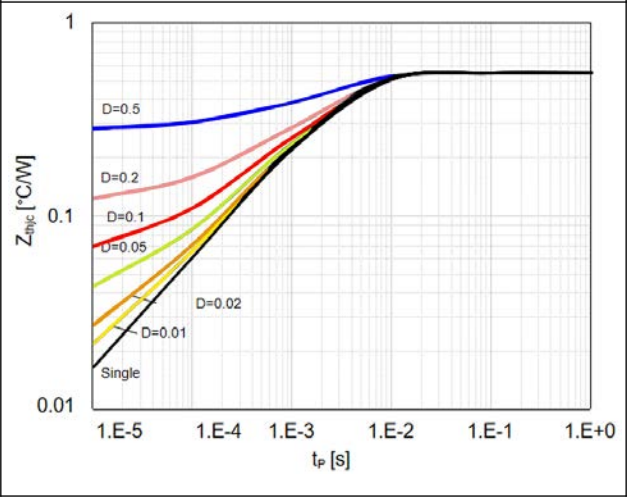
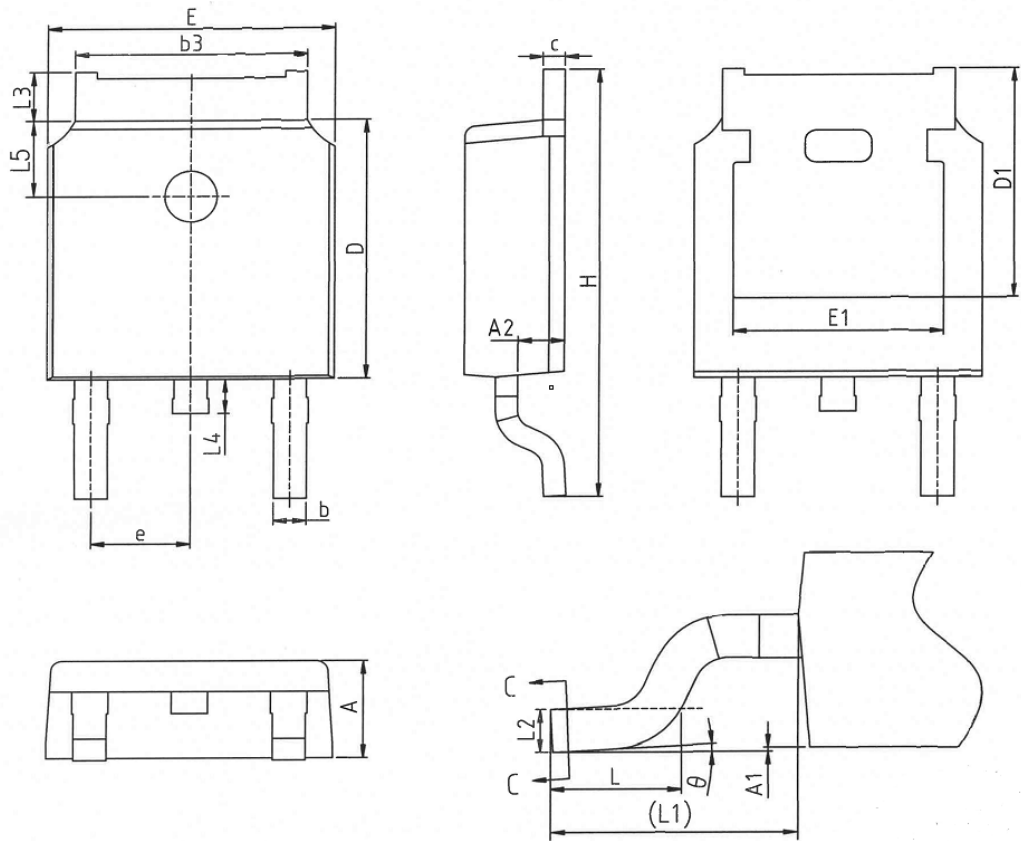


Figure 8. Transient Thermal Response Curve



Package Outlines

TO252NC



COMMON DIMENSIONS

SYMBOL	mm		
	MIN	NOM	MAX
A	2.20	2.30	2.38
A1	0.00	-	0.12
A2	0.97	1.07	1.17
b	0.68	0.78	0.90
b3	5.20	5.33	5.46
c	0.43	0.53	0.61
D	5.98	6.10	6.22
D1	5.30REF		
E	6.40	6.60	6.73
E1	4.63	-	-
e	2.286BSC		
H	9.40	10.10	10.50
L	1.38	1.50	1.75
L1	2.90REF		
L2	0.51BSC		
L3	0.88	-	1.28
L4	0.50	-	1.00
L5	1.65	1.80	1.95
θ	0°	-	8°

* Dimensions in millimeters

Package Marking and Ordering Information

Part Number	Top Marking	Package	Packing Method	Quantity
BCM120S20D2	BCM120S20D2	TO252NC	Tape&Reel	2500units

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